[0037] FIG. 4b is a cross-sectional view of the micro-switch 400 shown in FIG. 4a in its "activated" state;

[0038] FIG. 5 is a cross-sectional view of the micro-switch 400 shown in FIG. 4a, including dielectric spacers;

[0039] FIG. 6a is a cross-sectional view of the micro-switch 400 shown in FIG. 4a, including upper and lower mechanical stops 317, 328;

[0040] FIG. 6b is a cross-sectional view of the micro-switch 400 shown in FIG. 6a after final bonding;

[0041] FIG. 7 is a flow diagram showing the process flow steps used in the fabrication of the lid assembly 200 shown in FIG. 2a;

[0042] FIGS. 8a-l are cross-sectional views showing the process flow steps used in the fabrication of the lid assembly 200 shown in FIG. 2a;

[0043] FIG. 9 is flow diagrams showing the process flow steps used in the fabrication of the base assembly 220 shown in FIG. 2b;

[0044] FIGS. 10a-i are cross-sectional views showing the process flow steps used in the fabrication of the base assembly 220 shown in FIG. 2b; and

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[0045] FIGS. 11a-~~b~~c illustrate a wafer-scale bonding technique used to fabricate the micro-switch 400 shown in FIG. 4a.

DETAILED DESCRIPTION OF EMBODIMENTS

[0046] Although the MEMS device described below is a micro-switch, it should be understood by the reader that the present invention is not limited to a micro-switch, but also applies to other types of MEMS devices, including but not limited to optical switches, micro-relays, microdisplays, optical attenuators, variable optical attenuators, variable capacitors, phase shifters, surface acoustic wave devices, film bulk acoustic resonator (FBAR) devices, inductors, gyroscopes, accelerometers, pressure sensors, fluidic channels, chambers, resonators, strain sensors, rotary accelerometers, fiber optic